

# MOSFET

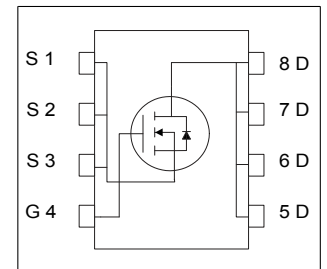
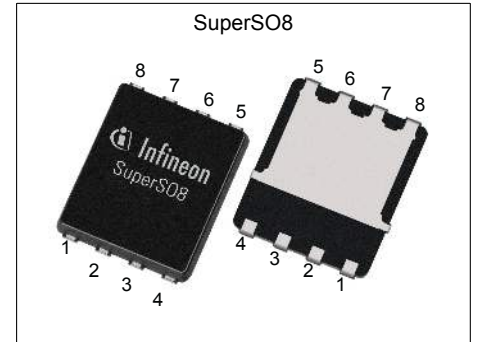
## OptiMOS™ 5 Power-Transistor, 80 V

### Features

- Optimized for high performance SMPS, e.g. sync. rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

### Product validation

Fully qualified according to JEDEC for Industrial Applications



RoHS

**Table 1 Key Performance Parameters**

| Parameter        | Value | Unit       |
|------------------|-------|------------|
| $V_{DS}$         | 80    | V          |
| $R_{DS(on),max}$ | 3.7   | m $\Omega$ |
| $I_D$            | 136   | A          |
| $Q_{oss}$        | 56    | nC         |
| $Q_G(0V..10V)$   | 46    | nC         |

| Type / Ordering Code | Package    | Marking  | Related Links |
|----------------------|------------|----------|---------------|
| BSC037N08NS5T        | PG-TDSON-8 | 037N08NT | -             |

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                    | Symbol            | Values |      |                 | Unit | Note / Test Condition   |
|--|-------------------|--------|------|-----------------|------|---|
|  |                   | Min.   | Typ. | Max.            |      |   |
| Continuous drain current <sup>1)</sup>       | $I_D$             | -      | -    | 136<br>96<br>22 | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=50\text{K/W}^2)$ |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$     | -      | -    | 544             | A    | $T_C=25\text{ °C}$  |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$          | -      | -    | 140             | mJ   | $I_D=50\text{ A}$ , $R_{GS}=25\text{ }\Omega$   |
| Gate source voltage                          | $V_{GS}$          | -20    | -    | 20              | V    | -   |
| Power dissipation                            | $P_{tot}$         | -      | -    | 136<br>3.0      | W    | $T_C=25\text{ °C}$<br>$T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^2)$  |
| Operating and storage temperature            | $T_j$ , $T_{stg}$ | -55    | -    | 175             | °C   | IEC climatic category;<br>DIN IEC 68-1: 55/175/56   |

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter   | Symbol     | Values |      |      | Unit | Note / Test Condition |
|---|------------|--------|------|------|------|-----------------------|
|   |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case, bottom                 | $R_{thJC}$ | -      | 0.7  | 1.1  | K/W  | -                     |
| Thermal resistance, junction - case, top                    | $R_{thJC}$ | -      | -    | 20   | K/W  | -                     |
| Device on PCB, 6 cm <sup>2</sup> cooling area <sup>2)</sup> | $R_{thJA}$ | -      | -    | 50   | K/W  | -                     |

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

| Parameter                        | Symbol        | Values |            |            | Unit          | Note / Test Condition   |
|----------------------------------|---------------|--------|------------|------------|---------------|---|
|                                  |               | Min.   | Typ.       | Max.       |               |   |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 80     | -          | -          | V             | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$   |
| Gate threshold voltage           | $V_{GS(th)}$  | 2.2    | 3          | 3.8        | V             | $V_{DS}=V_{GS}$ , $I_D=72\text{ }\mu\text{A}$   |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | 0.1<br>10  | 1<br>100   | $\mu\text{A}$ | $V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$<br>$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | 10         | 100        | nA            | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$  |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 3.2<br>4.4 | 3.7<br>5.3 | m $\Omega$    | $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$<br>$V_{GS}=6\text{ V}$ , $I_D=25\text{ A}$   |
| Gate resistance <sup>1)</sup>    | $R_G$         | -      | 1.3        | 2.0        | $\Omega$      | -   |
| Transconductance                 | $g_{fs}$      | 47     | 94         | -          | S             | $ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=50\text{ A}$  |

**Table 5 Dynamic characteristics**

| Parameter                                  | Symbol       | Values |      |      | Unit | Note / Test Condition  |
|--|--------------|--------|------|------|------|--|
|  |              | Min.   | Typ. | Max. |      |  |
| Input capacitance <sup>1)</sup>            | $C_{iss}$    | -      | 3200 | 4200 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$                                    |
| Output capacitance <sup>1)</sup>           | $C_{oss}$    | -      | 530  | 690  | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$                                    |
| Reverse transfer capacitance <sup>1)</sup> | $C_{rss}$    | -      | 25   | 44   | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$                                    |
| Turn-on delay time                         | $t_{d(on)}$  | -      | 14   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |
| Rise time                                  | $t_r$        | -      | 10   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |
| Turn-off delay time                        | $t_{d(off)}$ | -      | 26   | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |
| Fall time                                  | $t_f$        | -      | 7    | -    | ns   | $V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ ,<br>$R_{G,ext}=3\text{ }\Omega$ |

**Table 6 Gate charge characteristics<sup>2)</sup>**

| Parameter                          | Symbol        | Values |      |      | Unit | Note / Test Condition   |
|------------------------------------|---------------|--------|------|------|------|---|
|                                    |               | Min.   | Typ. | Max. |      |   |
| Gate to source charge              | $Q_{gs}$      | -      | 15   | -    | nC   | $V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge at threshold           | $Q_{g(th)}$   | -      | 9.0  | -    | nC   | $V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge <sup>1)</sup> | $Q_{gd}$      | -      | 10   | 15   | nC   | $V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Switching charge                   | $Q_{sw}$      | -      | 16   | -    | nC   | $V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total <sup>1)</sup>    | $Q_g$         | -      | 46   | 58   | nC   | $V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate plateau voltage               | $V_{plateau}$ | -      | 4.8  | -    | V    | $V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge total, sync. FET       | $Q_{g(sync)}$ | -      | 40   | -    | nC   | $V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$                    |
| Output charge <sup>1)</sup>        | $Q_{oss}$     | -      | 56   | 74   | nC   | $V_{DD}=40\text{ V}$ , $V_{GS}=0\text{ V}$                                  |

<sup>1)</sup> Defined by design. Not subject to production test

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

| Parameter                             | Symbol        | Values |      |      | Unit | Note / Test Condition  |
|---------------------------------------|---------------|--------|------|------|------|--|
|                                       |               | Min.   | Typ. | Max. |      |  |
| Diode continuous forward current      | $I_S$         | -      | -    | 124  | A    | $T_C=25\text{ °C}$   |
| Diode pulse current                   | $I_{S,pulse}$ | -      | -    | 544  | A    | $T_C=25\text{ °C}$   |
| Diode forward voltage                 | $V_{SD}$      | -      | 0.9  | 1.1  | V    | $V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$               |
| Reverse recovery time <sup>1)</sup>   | $t_{rr}$      | -      | 41   | 83   | ns   | $V_R=40\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$ |
| Reverse recovery charge <sup>1)</sup> | $Q_{rr}$      | -      | 36   | 72   | nC   | $V_R=40\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$ |

<sup>1)</sup> Defined by design. Not subject to production test

### 4 Electrical characteristics diagrams

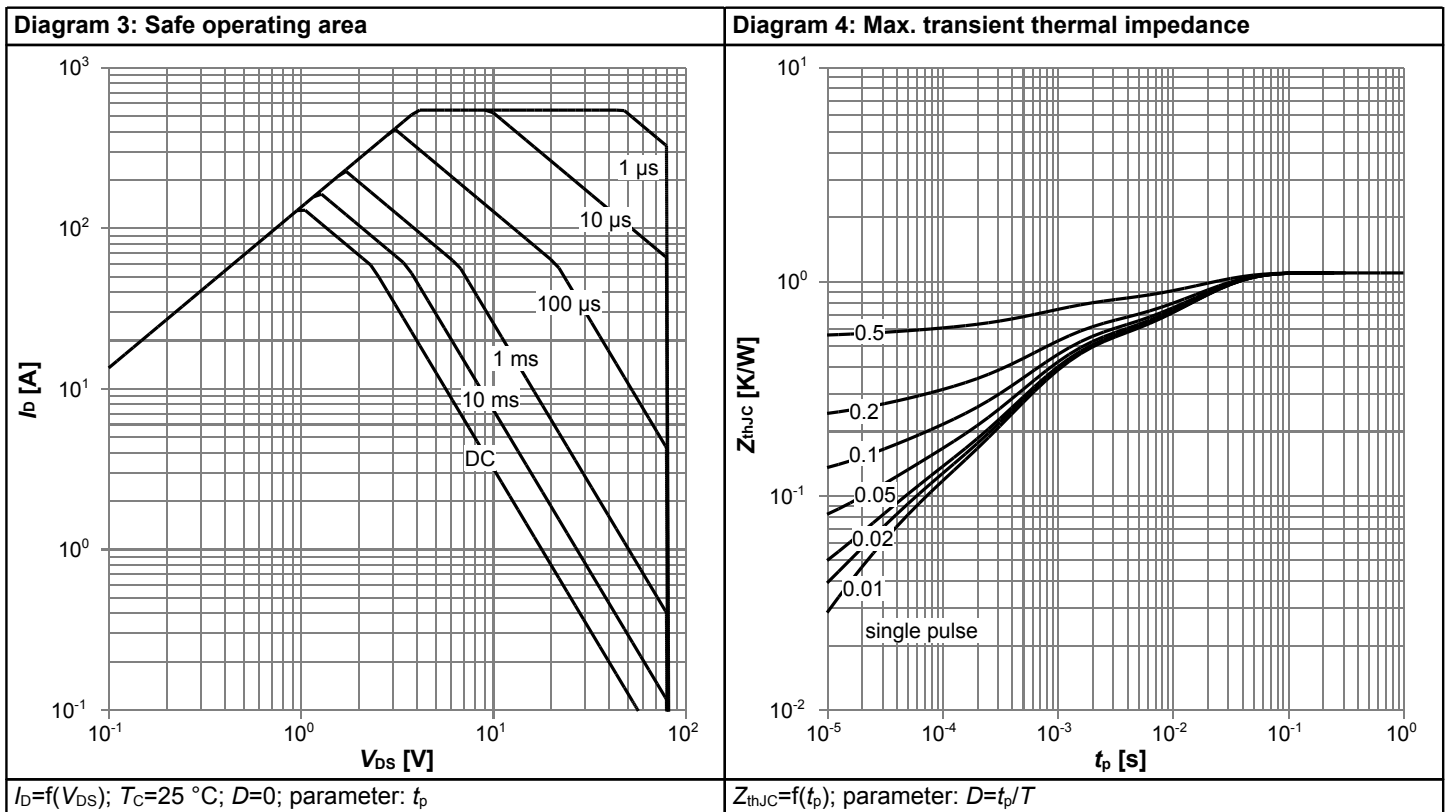
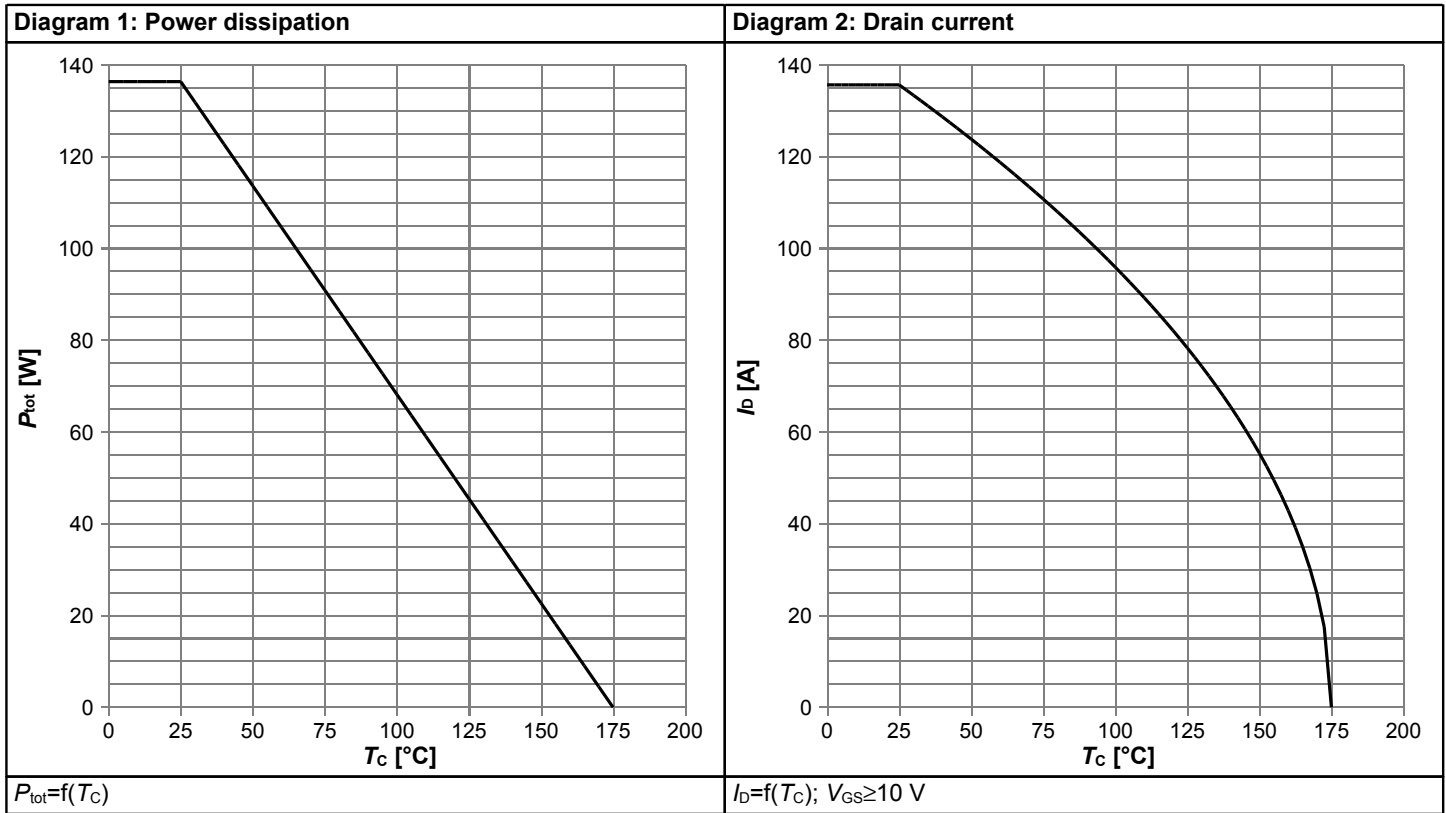
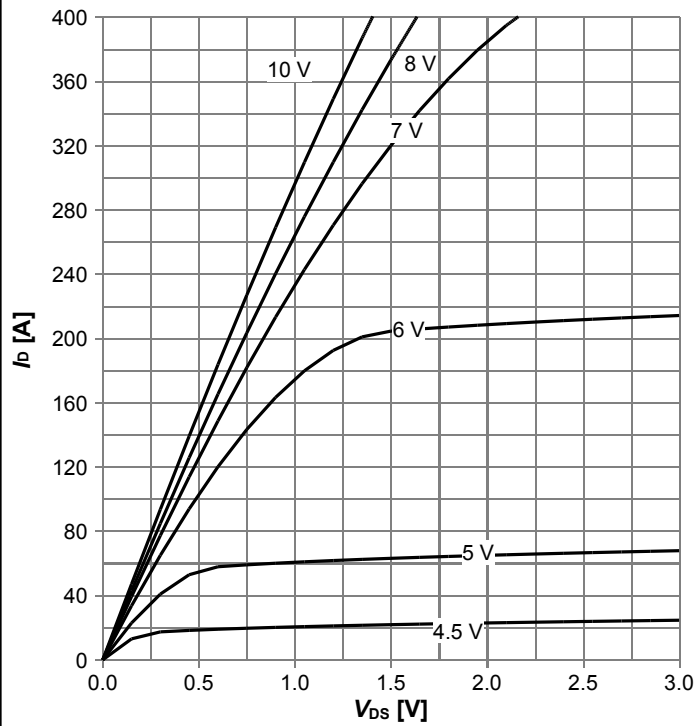
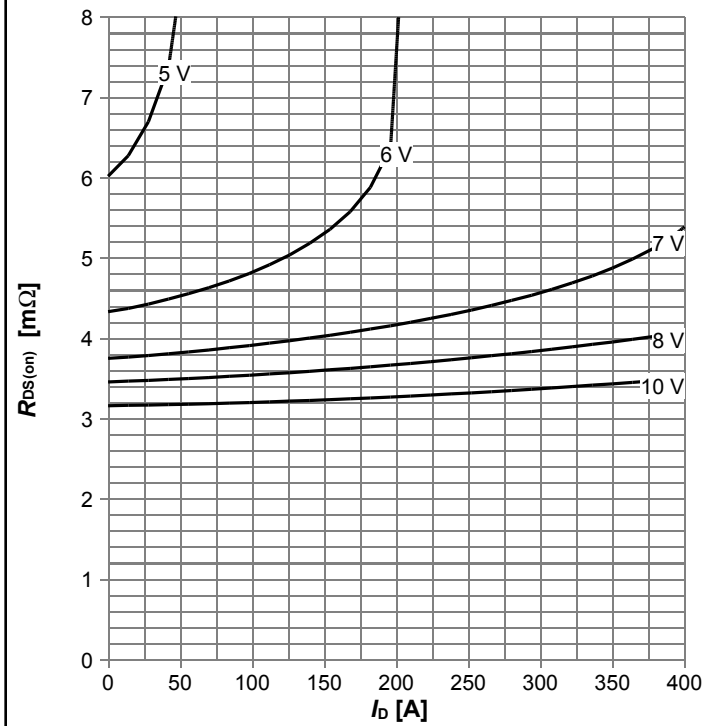


Diagram 5: Typ. output characteristics



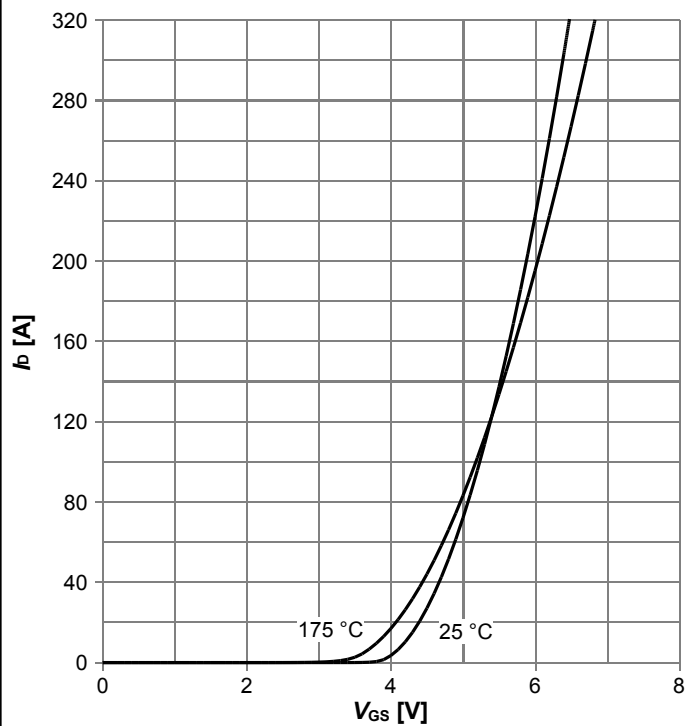
$I_D = f(V_{DS}); T_j = 25\text{ °C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



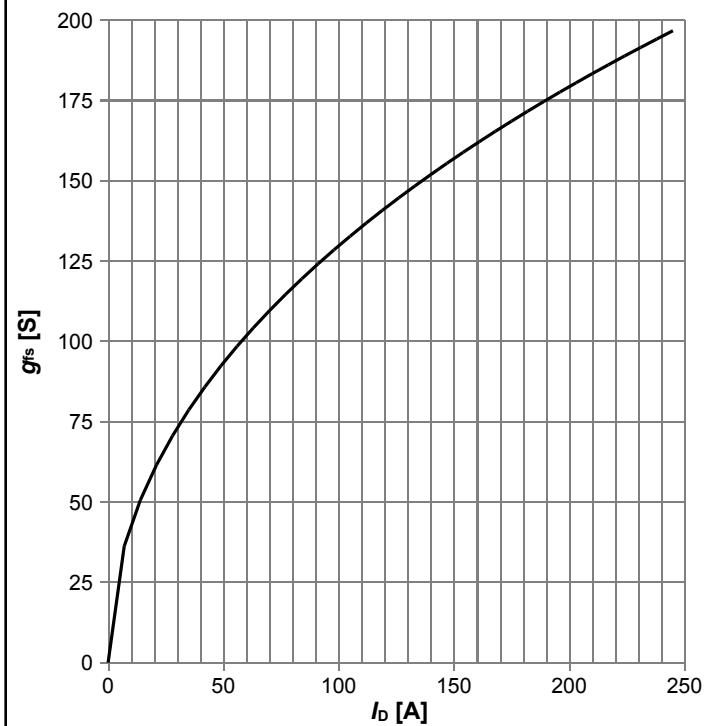
$R_{DS(on)} = f(I_D); T_j = 25\text{ °C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



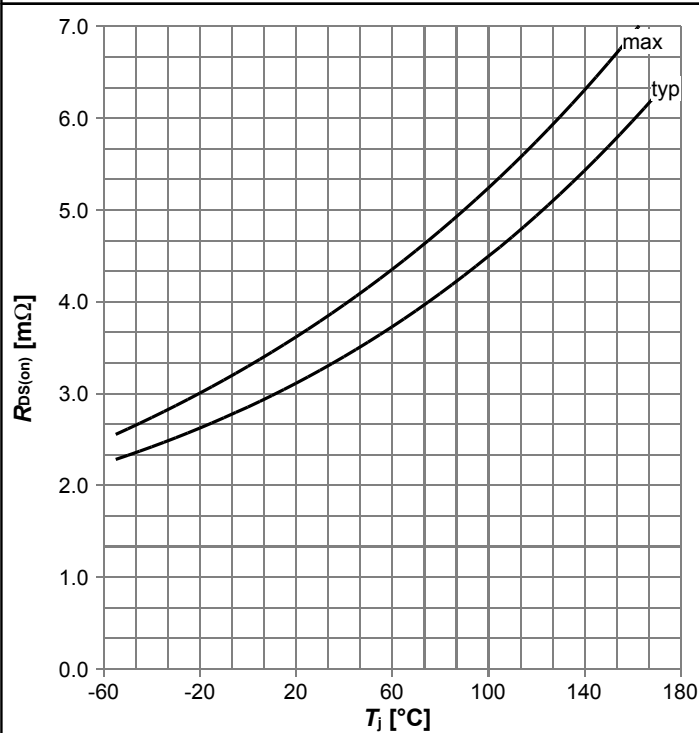
$I_D = f(V_{GS}); |V_{DS}| > 2 |I_D| R_{DS(on)max};$  parameter:  $T_j$

Diagram 8: Typ. forward transconductance



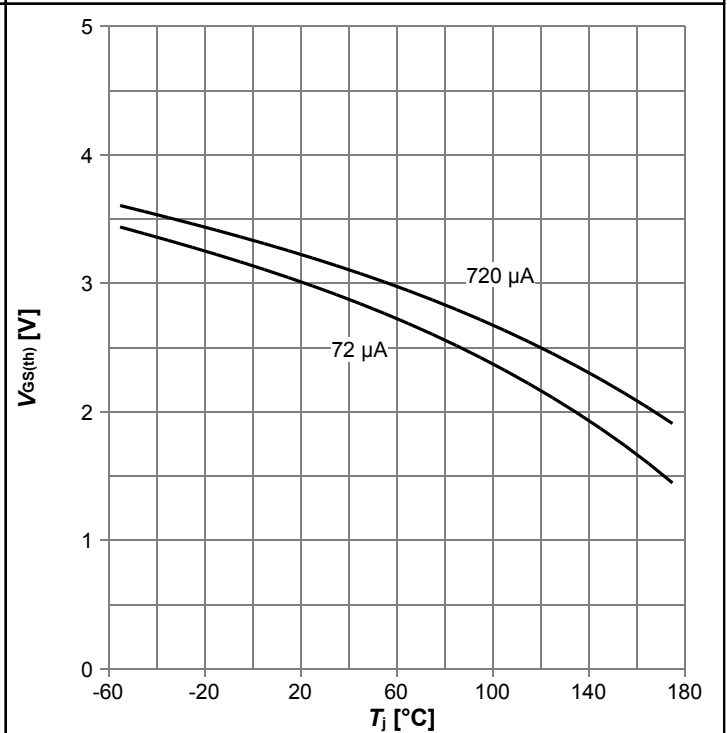
$g_{fs} = f(I_D); V_{DS} = 3\text{ V}; T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



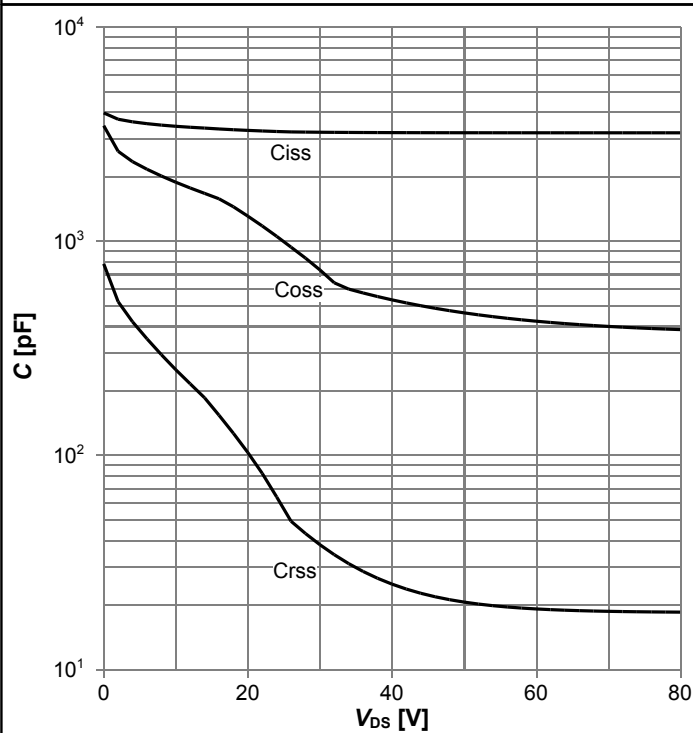
$R_{DS(on)}=f(T_j)$ ;  $I_D=50\text{ A}$ ,  $V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



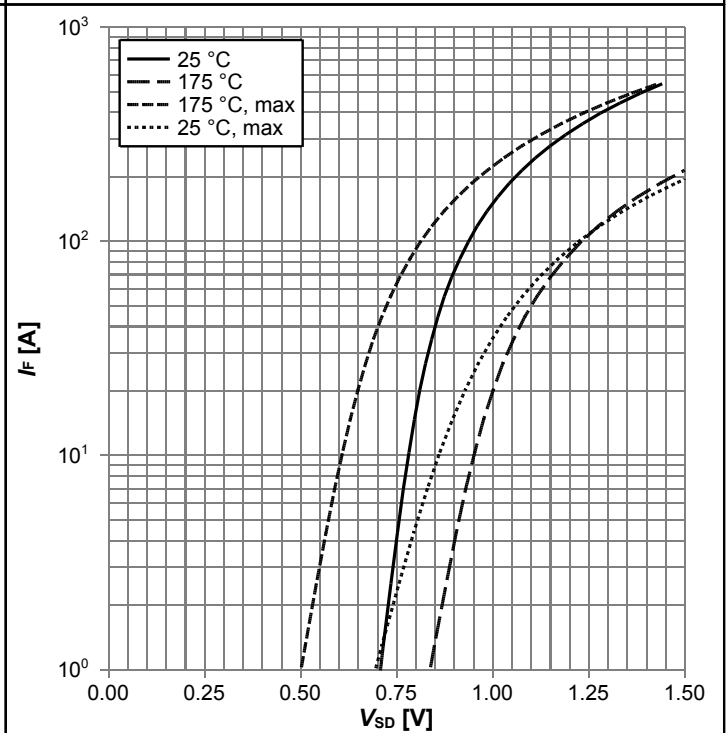
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



$C=f(V_{DS})$ ;  $V_{GS}=0\text{ V}$ ;  $f=1\text{ MHz}$

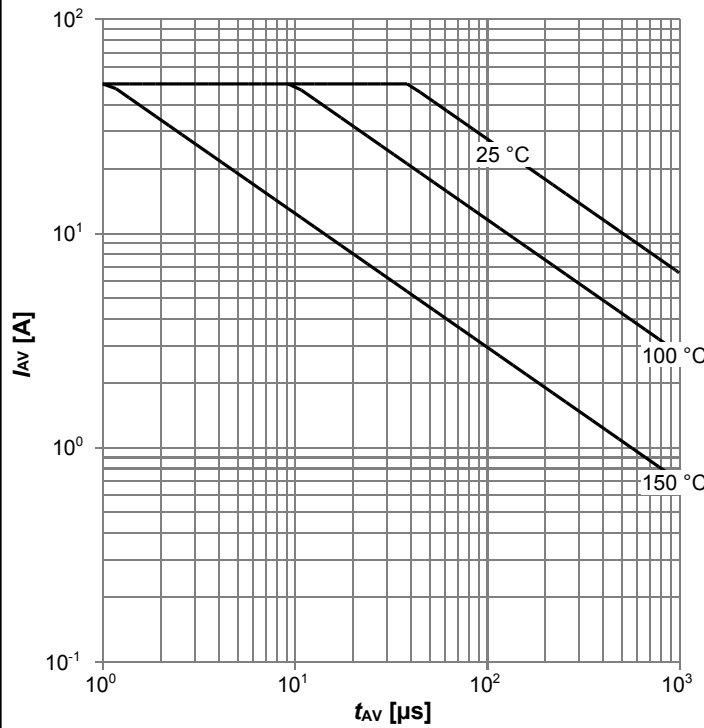
Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

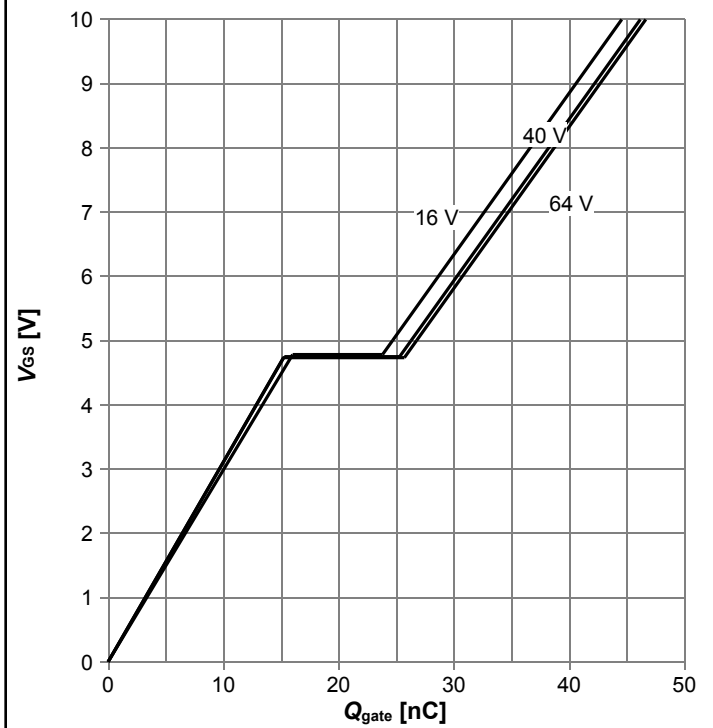


**Diagram 13: Avalanche characteristics**



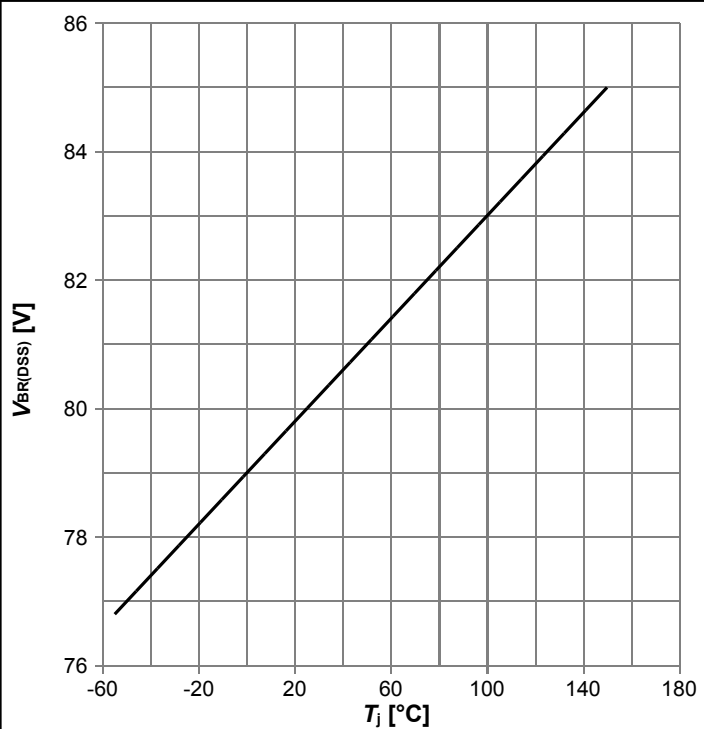
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j,start}$

**Diagram 14: Typ. gate charge**



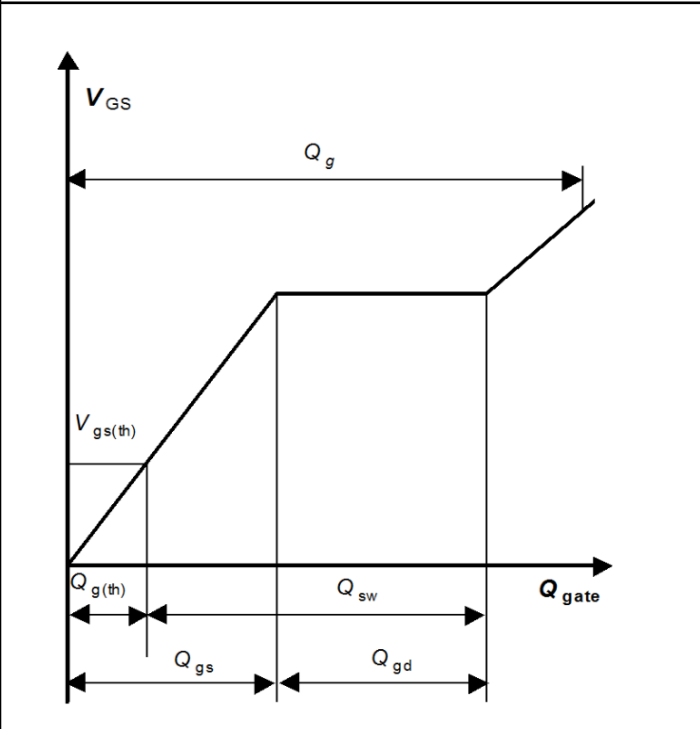
$V_{GS}=f(Q_{gate}); I_D=50 \text{ A pulsed}$ ; parameter:  $V_{DD}$

**Diagram 15: Drain-source breakdown voltage**



$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

**Diagram Gate charge waveforms**



## 5 Package Outlines



| DIM      | MILLIMETERS |      |
|----------|-------------|------|
|          | MIN         | MAX  |
| A        | 0.90        | 1.10 |
| b        | 0.31        | 0.54 |
| b1       | 0.02        | 0.22 |
| c        | 0.15        | 0.35 |
| D        | 5.15        | 5.49 |
| D1       | 4.95        | 5.35 |
| D2       | 3.70        | 4.40 |
| E        | 5.95        | 6.35 |
| E1       | 5.70        | 6.10 |
| E2       | 3.40        | 3.80 |
| e        | 1.27        |      |
| N        | 8           |      |
| L        | 0.45        | 0.71 |
| M        | 0.45        | 0.75 |
| $\theta$ | 8.5°        | 12°  |
| aaa      | 0.25        |      |
| eee      | 0.08        |      |

|                                    |
|------------------------------------|
| <b>DOCUMENT NO.</b><br>Z8B00003332 |
| <b>SCALE</b><br>0<br>2<br>4mm      |
| <b>EUROPEAN PROJECTION</b><br>     |
| <b>ISSUE DATE</b><br>10-04-2013    |
| <b>REVISION</b><br>04              |

Figure 1 Outline PG-TDSON-8, dimensions in mm

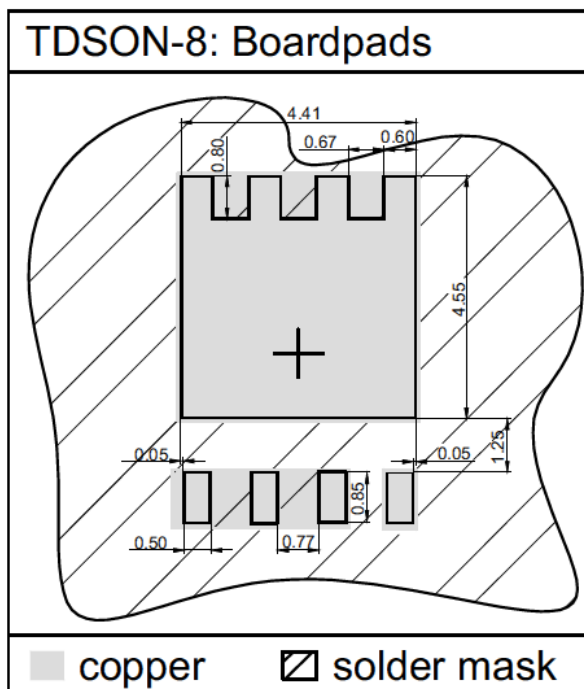


Figure 2 Outline Footprint (TDSO-8)

## Revision History

BSC037N08NS5T

**Revision: 2020-06-17, Rev. 2.2**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0      | 2019-01-22 | Release of final version                     |
| 2.1      | 2019-03-05 | Update Diagrams 8 and 9                      |
| 2.2      | 2020-06-17 | Update current rating                        |

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### Published by

**Infineon Technologies AG**

**81726 München, Germany**

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